

HAT2279N

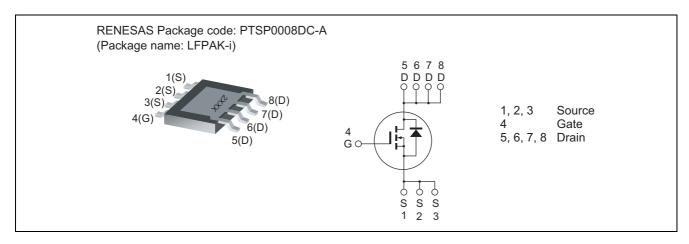
Silicon N Channel Power MOS FET Power Switching

REJ03G1596-0300 Rev.3.00 Oct 15, 2007

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 9.8 \ m\Omega \ typ. \ (at \ V_{GS} = 10 \ V)$
- Lead Free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	80	V	
Gate to source voltage	V _{GSS}	±20	V	
Drain current	I _D	30	А	
Drain peak current	I _{D(pulse)} Note1	120	А	
Body-drain diode reverse drain current	I _{DR}	30	А	
Avalanche current	I _{AP} Note 2	25	А	
Avalanche energy	E _{AR} Note 2	83	mJ	
Channel dissipation	Pch Note3	25	W	
Channel to Case Thermal Resistance	θch-C	5	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. $Tc = 25^{\circ}C$

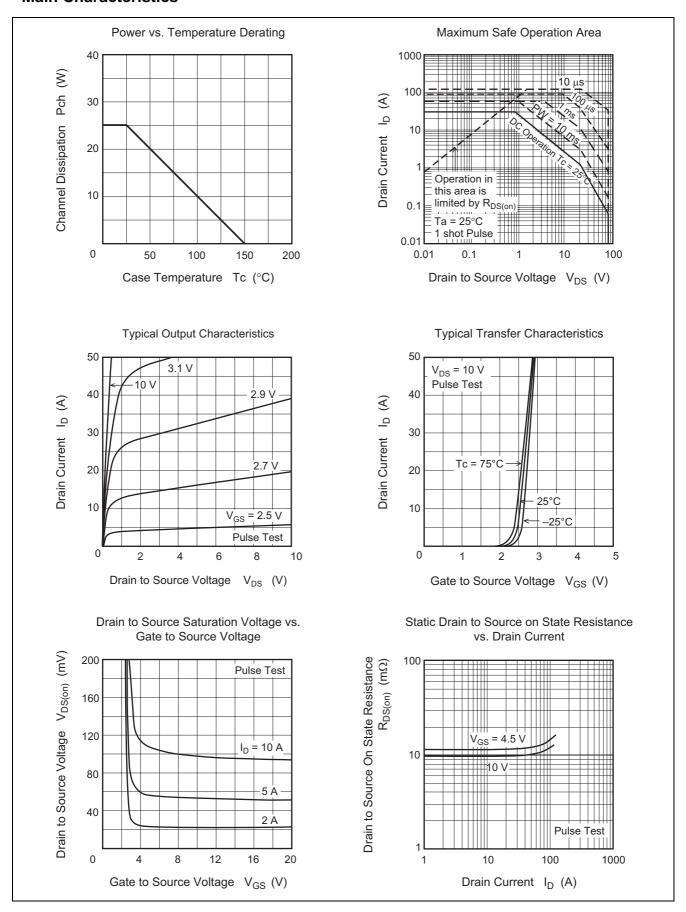
Electrical Characteristics

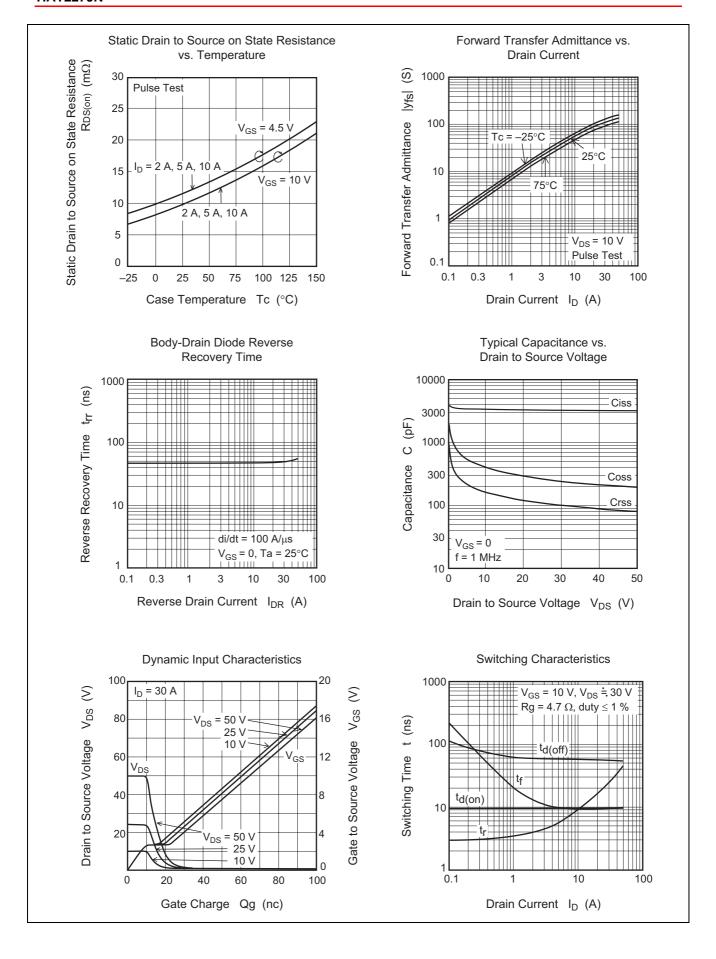
 $(Ta = 25^{\circ}C)$

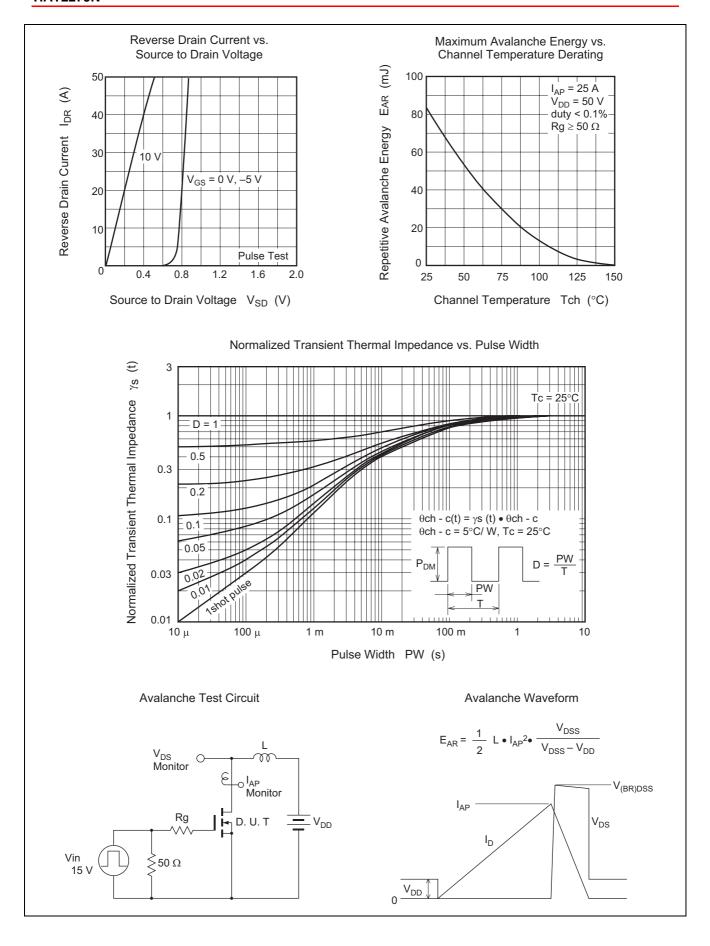
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	80	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	1	_	1	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.8	_	2.3	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	9.8	12.3	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	11.3	15.3	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	42	70	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	3520	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	410	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	160	_	pF	f = 1 MHz
Gate Resistance	Rg	_	0.5	_	Ω]
Total gate charge	Qg	_	60	_	nc	V _{DD} = 25 V
Gate to source charge	Qgs	_	9.5	_	nc	V _{GS} = 10 V
Gate to drain charge	Qgd	_	9.0	_	nc	$I_D = 30 \text{ A}$
Turn-on delay time	t _{d(on)}	_	9.5	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$
Rise time	t _r	_	14.5	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t _{d(off)}	_	56	_	ns	$R_L = 2 \Omega$
Fall time	t _f	_	9.5	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.83	1.08	V	IF = 30 A, V _{GS} = 0 Note4
Body-drain diode reverse recovery time	t _{rr}	_	50	_	ns	IF = 30 A, $V_{GS} = 0$ di _F / dt = 100 A/ μ s

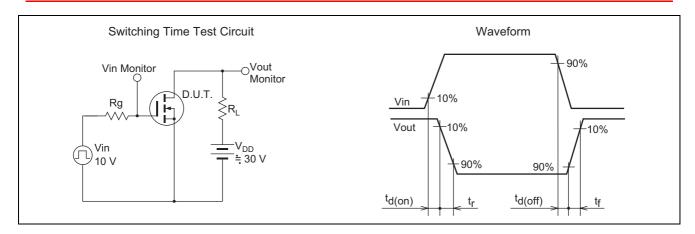
Notes: 4. Pulse test

Main Characteristics

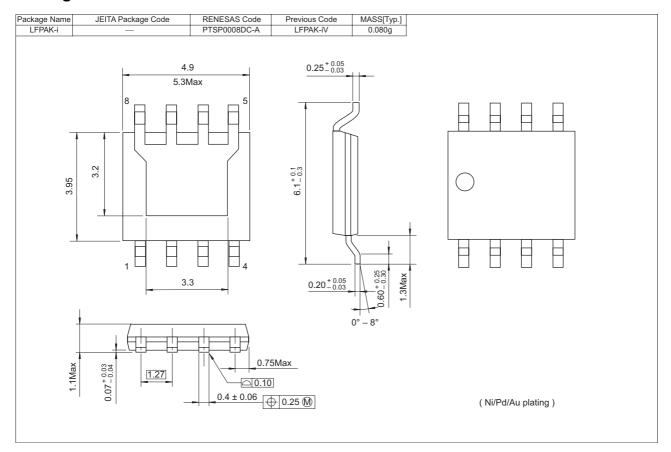








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2279N-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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